



**Erratum: ALD and Characterization of Aluminum Oxide Deposited on Si(100) Using Tris(diethylamino) Aluminum and Water Vapor [*J. Electrochem. Soc.*, **153**, C701 (2006)]**

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The authors are grateful to John Roth, at Research Resource Center of University of Illinois at Chicago, who provided help with the electron microscope and XPS. The authors are also grateful to Laurent Duquesne at American Air Liquide, Chicago, for help with

TDEAA characterization and in setting up the ALD reactor. They also thank Dr. John A. Belot, Jr., from the University of Nebraska-Lincoln for supplying the TDEAA precursor. This research was supported by NSF-GOALI grant no. 0329195.